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The invention relates to the semiconductor technology, in particular to the processes for semiconductor nanostructures obtaining.

Summary of the invention consists in that onto one of the surfaces of a semiconducting crystal, by photolithography, it is deposited a mask, it is carried out the electrochemical pickling and it is removed the mask. Novelty of the invention consists in that after removal of the mask it is additionally carried out the electrochemical pickling by light irradiation, the quanta energy of which exceeds the value of the semiconductor prohibited zone.

Claims: 1